

Title (en)
Methods for producing interconnects in semiconductor devices

Title (de)
Verfahren zur Herstellung von Verbindungen in Halbleitervorrichtungen

Title (fr)
Procédés de fabrication d'interconnexions dans des dispositifs à semi-conducteur

Publication
EP 2779224 A3 20141231 (EN)

Application
EP 14159975 A 20140314

Priority
US 201361799703 P 20130315

Abstract (en)
[origin: EP2779224A2] A method for producing interconnects on a workpiece includes obtaining a workpiece substrate having a feature, depositing a conductive layer in the feature, to partially or fully fill the feature, depositing a copper fill to completely fill the feature if the feature is partially filled by the conductive layer, applying a copper overburden, thermally treating the workpiece, and removing the overburden to expose the substrate and the metalized feature.

IPC 8 full level
H01L 21/768 (2006.01); **H01L 23/532** (2006.01)

CPC (source: CN EP KR US)
H01L 21/76849 (2013.01 - CN EP KR US); **H01L 21/76873** (2013.01 - CN EP KR US); **H01L 21/76877** (2013.01 - CN EP US);
H01L 21/76879 (2013.01 - US); **H01L 21/76882** (2013.01 - CN EP KR US); **H01L 21/76883** (2013.01 - CN EP KR US);
H01L 23/53209 (2013.01 - EP US); **H01L 23/53233** (2013.01 - CN EP KR US); **H01L 23/53238** (2013.01 - CN EP KR US);
H01L 23/53266 (2013.01 - CN US); **H01L 2221/1089** (2013.01 - CN EP US); **H01L 2924/0002** (2013.01 - EP US)

C-Set (source: EP US)
H01L 2924/0002 + H01L 2924/00

Citation (search report)

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- [Y] WO 2012133400 A1 20121004 - TOKYO ELECTRON LTD [JP], et al & US 2014030886 A1 20140130 - FUKUSHIMA TAKARA [JP], et al
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US11094587B2; WO2020118100A1

Designated contracting state (EPC)
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)
BA ME

DOCDB simple family (publication)
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CN 108695244 B 20230117; KR 102178622 B1 20201113; KR 20140113611 A 20140924; TW 201448119 A 20141216; TW I598996 B 20170911;
US 10062607 B2 20180828; US 2014287577 A1 20140925; US 2017047249 A1 20170216; US 9425092 B2 20160823

DOCDB simple family (application)
EP 14159975 A 20140314; CN 201410099406 A 20140317; CN 201810331694 A 20140317; KR 20140031320 A 20140317;
TW 103109957 A 20140317; US 201414211602 A 20140314; US 201615243600 A 20160822